

Appl. No. 10/709,666
Amdt. dated November 09, 2005
Reply to Office action of October 18, 2005

Amendments to the Specification:

Please replace Abstract of Disclosure with the following context:

- A method for programming a single-bit storage nonvolatile memory cell includes the
- 5 steps of: providing a single-bit storage nonvolatile memory cell having a channel region between a left bit line and a right bit line, a composite dielectric layer for storing digital data, and a word line overlying the composite dielectric layer; performing a left side electron injection on the single-bit storage nonvolatile memory cell by applying a relatively high word line voltage (V_{WL_HIGH}) to the word line, applying a relatively high
- 10 left bit line voltage (V_{LBL_HIGH}) to the left bit line, and applying a relatively low right bit line voltage (V_{RBL_LOW}) to the right bit line; and performing a right side electron injection-
~~on the single-bit storage nonvolatile memory cell~~ by applying the relatively high word line voltage (V_{WL_HIGH}) to the word line, applying a relatively low left bit line voltage-
(V_{LBL_LOW}) to the left bit line, and applying a relatively high right bit line voltage ($V_{RBL_}$
- 15 $HIGH$) to the right bit line.